

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|---------------------|
| L1 | 30 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:15 |
| L2 | 0 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and L1 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:15 |
| L3 | 327 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:15 |
| L4 | 0 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and L3 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:15 |
| L5 | 3 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and vcsl | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:16 |
| L6 | 4 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and ("vcsl" or (vertical near cavity)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:17 |
| L7 | 2 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and ("vcsl" or (vertical near cavity)) and (oxidat\$4 or oxidiz\$4) same (substrate or wafer or carrier or base or plate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:18 |
| L8 | 2 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and ("vcsl" or (vertical near cavity)) and (oxidat\$4 or oxidiz\$4) same (substrate or wafer or carrier or base or plate) and temperature | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/22 18:18 |

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|-----|------|---|---|----|----|---------------------|
| S1 | 369 | (oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:05 |
| S2 | 326 | (oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/18 11:22 |
| S3 | 54 | (oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support) and time | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/18 11:23 |
| S4 | 7 | (oxidiz\$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold\$4 or arm or support) and time and condensat\$4 | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/18 11:24 |
| S5 | 6712 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:06 |
| S6 | 143 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:07 |
| S7 | 0 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and temperature and thermistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:09 |
| S8 | 0 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and thermistor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:11 |
| S9 | 14 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and sensor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:11 |
| S10 | 5 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:26 |

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|-----|--------|--|---|----|----|---------------------|
| S11 | 1 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor) and graphite | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:28 |
| S12 | 0 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and ((layer or film) near stack) and (heat\$4 or thermal) and gas and ((heat or thermal) same sensor) and GaAs | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:34 |
| S13 | 37 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:35 |
| S14 | 3 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite and thermocouple | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:41 |
| S15 | 3 | (substrate or wafer or carrier or base) near9 (oxidiz\$4 near (layer or film)) and GaAs and graphite and thermocouple and laser | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:41 |
| S16 | 226127 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 08:34 |
| S17 | 3428 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz \$4 near9 (layer or film)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 08:36 |
| S18 | 886 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz \$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 08:36 |
| S19 | 23 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz \$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 08:58 |
| S20 | 23 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz \$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) and temperature | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 09:00 |

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|-----|-----|--|---|----|----|---------------------|
| S21 | 10 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) and temperature and (process with temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 09:04 |
| S22 | 1 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) and temperature and (process with temperature) and (record with temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 09:06 |
| S23 | 1 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) and temperature and (process with temperature) and record | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 09:08 |
| S24 | 10 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near gas) and temperature and (process with temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 09:08 |
| S25 | 5 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and ((holder or handler) with graphite) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:19 |
| S26 | 1 | (wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz\$4 near9 (layer or film)) and (heat\$4 or thermal\$4) near9 (device or circuit) and ((holder or handler) with graphite) and (thermal near conductivity) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:21 |
| S27 | 190 | ((holder or handler) with graphite) and (thermal near conductivity) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:21 |
| S28 | 54 | ((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:22 |
| S29 | 36 | ((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:22 |
| S30 | 32 | ((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler)) and (substrate or wafer or carrier or base or plate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/04/23 10:23 |

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|-----|--------|--|---|----|----|---------------------|
| S31 | 210573 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 anf (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat \$4) and temperature same (device or circuit) and (control same temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:04 |
| S32 | 209648 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 anf (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat \$4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:06 |
| S33 | 209639 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 anf (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat \$4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:06 |
| S34 | 209624 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 anf (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat \$4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:08 |
| S35 | 7 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat \$4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:09 |
| S36 | 110592 | (thermocouple or pyrometer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:36 |
| S37 | 37285 | (thermocouple or pyrometer) same (device or circuit) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:38 |

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| S38 | 590 | (thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:41 |
| S39 | 18 | (thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide)) and (oxidiz\$4 same ("GaAs" or (gallium near arsenide))) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:43 |
| S40 | 5 | (thermocouple or pyrometer) same (device or circuit) and (substrate or wafer or carrier or base or plate) same ("GaAs" or (gallium near arsenide)) and (oxidiz\$4 same ("GaAs" or (gallium near arsenide))) and graphite | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 09:55 |
| S41 | 1174 | (438/770.ccls.) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:22 |
| S42 | 110 | (438/770.ccls.) and (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:32 |
| S43 | 1354 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:32 |
| S44 | 764 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:33 |
| S45 | 362 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) and (oxidat\$4 same gas) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:34 |
| S46 | 257 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) and (oxidat\$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:40 |

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|-----|--------|---|---|----|----|---------------------|
| S47 | 180 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) and (oxidat\$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) and (control\$4 same temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:41 |
| S48 | 1 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) and (oxidat\$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) and (control\$4 same temperature) and vcsel | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:42 |
| S49 | 21 | (257/E21.079,E21.082,E21.267,E21.282,E21.283,E21.284,E21.287,E21.291,E21.301.ccls.) and (oxidat\$4 same (substrate or wafer or carrier or base or plate)) and (oxidat\$4 same gas) and (temperature near9 (substrate or wafer or carrier or base or plate)) and (control\$4 same temperature) and ((gallium near arsenide) or "GaAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:42 |
| S50 | 861 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:50 |
| S51 | 116480 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and ((gallium near arsenide) or "GaAs") or ((alumnium near arsenide) or "AlAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:51 |
| S52 | 5 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and ((gallium near arsenide) or "GaAs") and ((alumnium near arsenide) or "AlAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:52 |
| S53 | 49 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:53 |
| S54 | 48 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:54 |
| S55 | 33 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:54 |

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|-----|------|---|---|----|----|---------------------|
| S56 | 21 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat\$4 or oxidix\$4) near9 gas) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:54 |
| S57 | 20 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat\$4 or oxidix\$4) near9 gas) and (control\$4 near9 temperature) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:55 |
| S58 | 19 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat\$4 or oxidix\$4) near9 gas) and (control\$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:55 |
| S59 | 1 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat\$4 or oxidix\$4) near9 gas) and (control\$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base) and stack | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:56 |
| S60 | 19 | 438/770.ccls. and (substrate or wafer or carrier or base or plate or support) same (oxidiz\$4 or oxidat\$4) and (thermocouple or pyrometer) and (circuit or device) and (temperature same (holder or support or plate)) and ((oxidat\$4 or oxidix\$4) near9 gas) and (control\$4 near9 temperature) and gas near9 (substrate or wafer or carrier or base) and (heat or thermal) near9 (substrate or wafer or carrier or base or plate or support) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/09/16 10:56 |
| S61 | 5 | (substrate or wafer or carrier or base or plate or support) same oxidiz\$4 and (heat\$4 or thermal\$4) near9 (device or circuit) and (oxidat\$4 near9 gas) and (time same oxidat\$4) and temperature same (device or circuit) and (control same temperature) and (substrate or wafer or carrier or base or plate or support) near9 stack and (process near9 temperature) and ((gallium near arsenide) or "GaAs") and ((aluminum near arsenide) or "AlAs") | US-PGPUB | OR | ON | 2008/09/16 11:05 |
| S62 | 5183 | vcsl same (substrate or wafer or carrier or base or plate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 08:52 |

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| S63 | 440 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 08:53 |
| S64 | 327 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:02 |
| S65 | 4 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (oxidat\$4 or oxidiz\$4) near3 gas | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:02 |
| S66 | 95 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:42 |
| S67 | 37 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:43 |
| S68 | 33 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:43 |
| S69 | 30 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:44 |
| S70 | 30 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:45 |

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| S71 | 7 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 09:48 |
| S72 | 0 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber and (438/463,487,535,662,770,940.ccls.) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 10:04 |
| S73 | 0 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber and chung.inv. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 10:05 |
| S74 | 0 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber and gutt.inv. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2009/05/21 10:05 |
| S75 | 0 | vcsl same (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber .clm. | US-PGPUB | OR | ON | 2009/05/21 10:06 |
| S76 | 13957 | vcsl amd (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber .clm. | US-PGPUB | OR | ON | 2009/05/21 10:06 |

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| S77 | 4 | vcSEL and (substrate or wafer or carrier or base or plate) same (oxidiz\$4 or oxidat\$4) and temperature and (gas same (substrate or wafer or carrier or base or plate)) and (layer or film) same stack and (oxidiz\$4 or oxidat\$4) near4 (layer or film) and (heat\$4 or thermal or anneal\$4) same (substrate or wafer or carrier or base or plate) and ((gallium near arsenide) or "GaAs") and chamber .clm. | US-PGPUB | OR | ON | 2009/05/21 10:06 |
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